XIN XIN

Address: 4286 Shadow Creek Circle, Oviedo, FL 32765 Homepage: https://xinx2013.github.io/

Research Interests

My research focuses on high-performance memory in computer systems, e.g., main memory (DRAM) performance/power/reliability, processing-in-memory (PIM)/near-data-processing (NDP), hybrid DRAM-NVM system, and memory-based accelerators. I also have broad research/working experiences spanning from computer architecture to integrated circuit design to semiconductor devices.

PROFESSIONAL EXPERIENCES

University of Central Florida Assistant Professor

Alibaba Group Research Intern

Huada Electronic Design Co., Ltd. Digital Design Engineer

University of Pittsburgh Graduate Research Assistant

Tsinghua University Graduate Research Assistant

EDUCATION

University of Pittsburgh Ph.D. in Electrical and Computer Engineering Advisor: Jun Yang

Tsinghua University

M.E. in Electrical Engineering (Integrated Circuit) Advisors: Tianling Ren and Yi Yang

Lanzhou University

B.S. in Electrical Engineering (Microelectronics)

PUBLICATIONS

- C1 Xin Xin, Wanyi Zhu, and Li Zhao, "Architecting DDR5 DRAM Caches for Non-Volatile Memory Systems," in Proceedings of the 59th ACM/IEEE Design Automation Conference. (DAC 2022)
- C2 Xin Xin, Yanan Guo, Youtao Zhang, and Jun Yang, "SAM: Accelerating Strided Memory Accesses," in Proceedings of the 54th IEEE/ACM International Symposium on Microarchitecture. (MICRO 2021)
- C3 Xin Xin, Youtao Zhang, and Jun Yang, "Reducing DRAM Access Latency via Helper Rows," in Proceedings of the 57th ACM/IEEE Design Automation Conference. (DAC 2020)

Email: xin.xin@ucf.edu Phone: (+1) 407 823 1753

> Beijing, China Spe. 2013 - Jul. 2016

Pittsburgh, PA Jan. 2018 - Jun. 2023

Beijing, China Sep. 2013 - Jul. 2016

Lanzhou, China Sep. 2009 - Jul. 2013

Aug. 2023 - Now Sunnyvale, CA

Orlando, FL

Aug. 2021 - Dec. 2021 Beijing, China

Aug. 2016 - Aug. 2017

Pittsburgh, PA Jan. 2018 - Jul. 2023

- C4 <u>Xin Xin</u>, Youtao Zhang, and Jun Yang, "ELP2IM: Efficient and Low Power Bitwise Operation Processing in DRAM," in Proceedings of the 26th International Symposium on High-Performance Computer Architecture. (HPCA 2020)
- C5 <u>Xin Xin</u>, Youtao Zhang, and Jun Yang, "ROC: DRAM-based Processing with Reduced Operation Cycles," in Proceedings of the 56th ACM/IEEE Design Automation Conference. (DAC 2019)
- C6 Yanan Guo, <u>Xin Xin</u>, Youtao Zhang, Jun Yang, "Leaky Way: A Conflict-Based Cache Covert Channel Bypassing Set Associativity," in Proceedings of the 55th IEEE/ACM International Symposium on Microarchitecture. (MICRO 2022)
- C7 Congming Gao, <u>Xin Xin</u>, Youyou Lu, Youtao Zhang, Jun Yang, and Jiwu Shu, "ParaBit: Processing Parallel Bitwise Operations in NAND Flash Memory based SSDs," in Proceedings of the 54th IEEE/ACM International Symposium on Microarchitecture. (MICRO 2021)

Prepared/Under Review

- U1 <u>Xin Xin</u>, Yanan Guo, Youtao Zhang, and Jun Yang, "ReBACK: Recouping Hidden Bandwidth in Chip-Kill ECC," submitted to HPCA.
- U2 <u>Xin Xin</u>, Yanan Guo, Youtao Zhang, and Jun Yang, "RIO: A DRAM-based Memory Substrate with Reconfigurable I/O Width," in preparation for TCAD.

Prior to PhD

- J1 Xin Xin, Haiming Zhao, Huiwen Cao, He Tian, Yi Yang, and Tianling Ren, "In situ observation of electrical property of thin-layer black phosphorus based on dry transfer method," Applied Physics Express, 2016, 9(4): 45202.
- J2 Ziming Zhang^{*}, <u>Xin Xin^{*}</u>, Qingfeng Yan, Qiang Li, Yi Yang, and Tianling Ren, "Two-step heating synthesis of sub-3 millimeter-sized orthorhombic black phosphorus single crystal by chemical vapor transport reaction method," Science China Materials, 2016, 59(2): 122-134. (* eequal contribution)

TEACHING EXPERIENCES

Teaching Assistant, University of Pittsburgh ECE 1869 - Introduction to Electrical Engineering ECE 1212 - Electronic Circuit Design Laboratory ECE 1110 - Computer Organization and Architecture ECE 0202 - Embedded Processors and Interfacing

Guest Lecturer, University of Pittsburgh ECE 2162 - Computer Architecture

RESEARCH EXPERIENCES

1. Bandwidth Efficiency Optimization

- Exploring under-utilized resources in commodity DRAM memories to improve bandwidth efficiency for specific applications with irregular access patterns, e.g., strided accesses and metadata accesses (C2, U1).
- We employed the unused internal bandwidth in server memories to tackle the over-fetching problem of strided memory accesses with near-zero hardware overhead.
- We leveraged the under-utilized channel bandwidth in large memory subsystems to mitigate the metadata overhead with negligible hardware overhead.

2. In-Place Processing in Memory

- Exploiting the intrinsic architecture of commodity DRAM memories to enable logic operations, e.g., AND and OR, inside DRAM chips and avoid redundant data movement (C3, C4, C7).
- We employed the parasitic capacitance on bitlines to develop a Boolean logic function for input variables located in DRAM cells.

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Pittsburgh, PA Jan. 2021 - May 2021 Aug. 2020 - Dec. 2020 Jan. 2020 - May 2020 Aug. 2019 - Dec. 2019

Pittsburgh, PA Aug. 2022 - Dec. 2022

Jan. 2018 - Present

Aug. 2020 - Present

• We augmented the cells with specific components to implement bulk logic operations with reduced latency and high energy efficiency.

3. Hybrid DRAM-NVM Memory Performance Optimization

- Reducing the performance penalty for an Optane system under the memory mode where DRAM is used as an off-chip cache for NVM (C1, U2).
- We allocated a dedicated channel for tag transfer to reduce the miss overhead.
- We proposed a novel swap operation to mitigate the writeback overhead.

4. Memory Latency Optimization

- Reducing the overhead of restoring charges back to DRAM cells, which accounts for a significant proportion of a row access cycle (C5).
- We repurposed the novel Row-Clone operations in recent PIM designs for restore truncation, i.e., cloning a row and selectively discarding the copy to avoid the restore.
- We augmented the proposed design by increasing the reuse possibility of the copied row.

5. Integrated Circuit & Device Design

- Designing and characterizing novel integrated circuits and semiconductor devices, with a focus on their electrical properties, e.g., on-off ratio and mobility (J1, J2).
- We set up a manufacturing process, including photolithography, deposition, plasma etching, etc., for device fabrication using emerging 2-dimensional materials such as black phosphorus (BP).
- We discovered that the electrical conduction of BP devices is time-dependent and exhibits an irregular reinstating phase.

Honors And Awards

University of Pittsburgh EGSO Travel Grant	2021
NSF/HPCA Travel Grant	2020
DAC 2020 Young Student Fellow	2020
Graduated with the Highest Honor set by the Government of Beijing	2016
Graduated with the Highest Honor set by Lanzhou University	2013

PROFESSIONAL SERVICES

Reviewer

IEEE Computer Architecture Letters Transactions on Embedded Computing Systems Transactions on Parallel and Distributed Systems Journal of Systems Architecture

Volunteer Student Assistant: MICRO 2020

TALKS

Architecting DDR5 DRAM Caches for Non-Volatile Memory Systems. DAC 2022
Improving the Next-Generation (DDR5) Optane Memory. Alibaba Group 2021
Accelerating Strided Memory Accesses. MICRO 2021
Reducing DRAM Access Latency via Helper Rows. DAC 2020
Efficient and Low Power Bitwise Operation Processing in DRAM. HPCA 2020
DRAM-based Processing with Reduced Operation Cycles. DAC 2019

Jan. 2014 - May. 2016

Aug. 2021 - Present

Aug. 2020 - May 2021